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Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-14. (Canceled)

15. (Currently amended) A semiconductor device comprising:

a substrate, and

a multilayer formed on the substrate, the multilayer comprising a plurality of semiconductor elements and a plurality of dummy semiconductor elements, and

a semiconductor element area on the substrate, which includes a the plurality of the semiconductor elements, and a dummy area on the substrate, which includes a plurality of the dummy semiconductor elements, the semiconductor element area being surrounded by the dummy area the plurality of dummy semiconductor elements,

wherein each of the plurality of semiconductor elements includes a capacitor which is comprised of a bottom electrode, a first dielectric layer on the bottom electrode and a top electrode on the first dielectric layer, and the first dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements includes a dummy capacitor which is comprised of a dummy bottom electrode, a second dielectric layer on the dummy bottom electrode and a dummy top electrode on the second dielectric layer, and the second dielectric layer is composed of a material selected from a dielectric material having a dielectric constant of 100 or more and a ferroelectric material,

wherein each of the plurality of dummy semiconductor elements is located so that a space between the electrode and the dummy electrode is in a predetermined range, and

wherein the multilayer is produced by a method comprising:

forming a dielectric film for the first dielectric layer and the second dielectric layer;
forming an electrically conductive film on the dielectric film;

and

etching the electrically conductive film so as to form the electrode and the dummy electrode.

16. (Previously presented) A semiconductor device according to claim 15, wherein the predetermined range of the space is between $0.3\mu\text{m}$ and $14\mu\text{m}$.
17. (Previously presented) A semiconductor device according to claim 15, wherein remnant polarization in the capacitor is in the range of 13 to $15 \mu\text{C}/\text{cm}^2$.
18. (Previously presented) A semiconductor device according to claim 15, wherein the first dielectric layer and the second dielectric layer are composed of a material selected from $\text{SrBi}_x\text{Ta}_x\text{O}_y$, $\text{Ba}_x\text{Sr}_{1-x}\text{TiO}_x$, $\text{Pb}(\text{Zr}_{1-x}\text{Ti}_x)\text{O}_3$, $\text{SrBi}_2(\text{Ta}_{1-x}\text{Nb}_x)_2\text{O}_9$ or $\text{Bi}_4\text{Ti}_3\text{O}_{12}$, where $0 \leq x \leq 1$.